Patterned Silver Nanowire Network for CdSe@CdZnS/ZnS Green Quantum Dot Light-Emitting Diodes

Chia-Yu Lin, Tzu-Hsu Wen, and Chun-Yuan Huang*
Department of Applied Science, National Taitung University
**E-mail address: laputa@nttu.edu.tw*

Table 1. The structure and device performance of QLEDs

Structure	L_{max} **(cd/m^2)**	**CE (cd/A)**
NOA63/AgNW/PEDOT:PSS*1/TFB(10mg/ml)/G-QD/MgZnO/Al	33945	17.7
NOA63/AgNW/PEDOT:PSS*1/TFB(20mg/ml)/G-QD/MgZnO/Al	2614.2	1.6
NOA63/AgNW/PEDOT:PSS*3/TFB(10mg/ml)/G-QD/MgZnO/Al	72922	27.8
NOA63/AgNW/PEDOT:PSS*3/TFB(20mg/ml)/G-QD/MgZnO/Al	7225.6	9.6

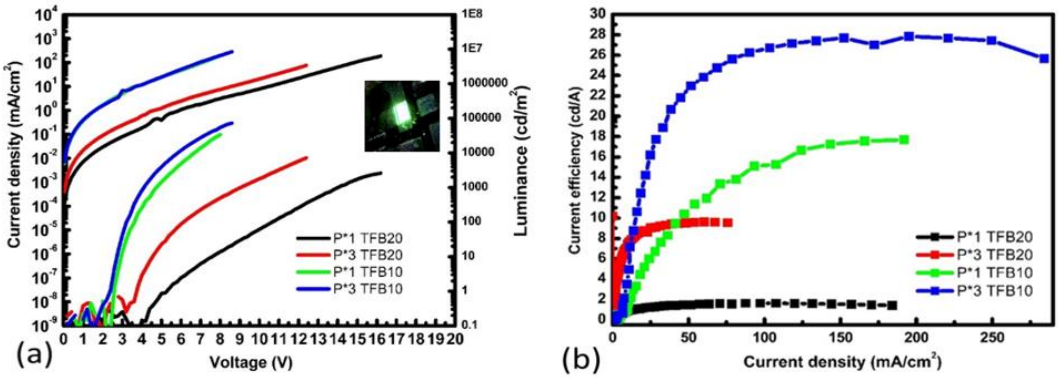

Fig. 1 (a) *J*–*V*–*L* and (b) *J*–CE characteristics of the QLED. Inset of (a) shows the emission of a QLED under operation.

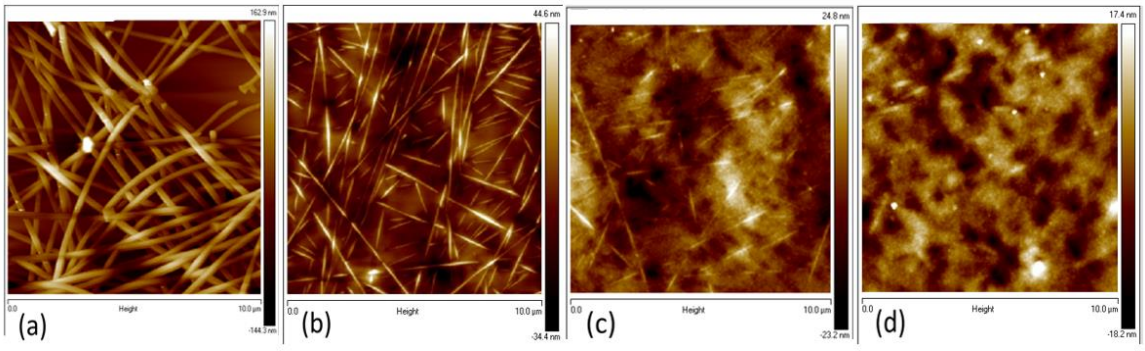

Fig. 2 Atomic force microscopy (AFM) images of the surface of (a) the raw AgNW electrode, (b) the AgNW/polyurethane composite film, and a composite film coated with (c) one layer and (d) three layers of PEDOT:PSS.